

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

*Listing of Claims*

## Claim 1 (Currently Amended)

A method for forming an adhesion between dielectric layers, the method comprising:  
providing a first dielectric layer; and  
in-situ forming a first portion of a second dielectric layer on said first dielectric layer, and a second portion of said second dielectric layer on said first portion, wherein said first portion has a dielectric constant in the range of about 2.8 to 3.5 and a thickness that is less than about 10 angstroms, said second portion has a dielectric constant in the range of 1.1 to 3 and a thickness that is thicker than said thickness of said first portion, and said first portion comprises carbon therein. ~~second dielectric layer having a first portion on said first dielectric layer and a second portion on said first portion, wherein said first portion has a first dielectric constant higher than said second portion has and said first portion comprises carbon.~~

## Claim 2 (Cancelled)

## Claim 3 (Currently Amended)

The method according to claim 1, wherein the in-situ forming step ~~having~~ has at least a process condition for forming said first portion and said second portion.

## Claim 4 (Original)

The method according to claim 3, wherein the in-situ forming step having said process condition comprises:

executing a chemical vapor deposition having a first bias; and  
executing said chemical vapor deposition having a second bias, wherein said first bias is higher than said second bias.

## Claim 5 (Original)

The method according to claim 3, wherein the in-situ forming step having said process condition comprises:

executing a chemical vapor deposition having a first HFRF for forming said first portion; and  
executing said chemical vapor deposition having a second HFRF, wherein said first HFRF is higher than said second HFRF.

## Claim 6 (Original)

The method according to claim 3, wherein the in-situ forming step having said process condition comprises:

executing a chemical vapor deposition having a first precursor for forming said first portion;  
and

executing said chemical vapor deposition having a second precursor, wherein the amount of said first precursor is less than the amount of said second precursor.

## Claim 7 (Original)

The method according to claim 1, wherein the in-situ forming step comprises plasma enhanced chemical vapor deposition (PECVD).

## Claim 8 (Currently Amended)

A method for forming an adhesion between dielectric layers, the method comprising:  
providing a first dielectric layer; and  
in-situ forming a second dielectric layer having a first portion on said first dielectric layer and a second portion on said first portion, wherein said first portion has a dielectric constant in the range of about 2.8 to 3.5 and said second portion has a dielectric constant in the range of about 1.1 to 3, ~~wherein~~ said first portion has a hardness higher than that of said second portion, ~~[[has]]~~ and said first portion comprises carbon.

## Claim 9 (Original)

The method according to claim 8, wherein said first dielectric layer has a dielectric constant which is higher than said second dielectric layer.

## Claim 10 (Original)

The method according to claim 8, wherein the in-situ forming step at least comprises: executing a chemical vapor deposition having a first bias for forming said first portion; and executing said chemical vapor deposition having a second bias for forming said second portion, wherein said first bias is higher than said second bias.

## Claim 11 (Previously Presented)

The method according to claim 8, wherein the in-situ forming step at least comprises: executing a chemical vapor deposition having a first HFRF for forming said first portion; and executing said chemical vapor deposition having a second HFRF for forming said second portion, wherein said first HFRF is higher than said second HFRF.

## Claim 12 (Cancelled)

## Claim 13 (Previously Presented)

The method according to claim 8, wherein the in-situ forming step comprises: executing a chemical vapor deposition having a first process condition; and executing said chemical vapor deposition having a second process condition, wherein said second process condition forming said second portion having a dielectric constant smaller than said first process condition forming said first portion.

## Claim 14 (Original)

The method according to claim 13, wherein said executing said chemical vapor deposition is plasma enhanced chemical vapor deposition (PECVD).

## Claim 15 (Currently Amended)

[[An]] A structure of enhanced-inter-adhesion dielectric layers, the structure comprising:  
a first dielectric layer; and  
a second dielectric layer having a first portion on said first dielectric layer and a second portion on said first portion, wherein said first portion has a [[first]] dielectric constant ~~around~~ in the range of about 2.8 to 3.5 and higher than a dielectric constant of said second portion which is in the range of about 1.1 to 3, and the thickness of said first portion is less than about 10 angstroms which is less than the thickness of said second portion. ~~and said first portion comprises carbon.~~

## Claim 16 (Original)

The structure according to claim 15, wherein said first dielectric layer is silicon nitride (SiN).

## Claim 17 (Original)

The structure according to claim 15, wherein said first dielectric layer is silicon carbide (SiC).

## Claim 18 (Cancelled)